

# Fei Zhuge

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

75  
papers

3,069  
citations

32  
h-index

54  
g-index

79  
ext. papers

3,430  
ext. citations

5.2  
avg, IF

4.96  
L-index

#	Paper	IF	Citations
75	Hybrid oxide brain-inspired neuromorphic devices for hardware implementation of artificial intelligence. <i>Science and Technology of Advanced Materials</i> , <b>2021</b> , 22, 326-344	7.1	7
74	All-Optically Controlled Memristor for Optoelectronic Neuromorphic Computing. <i>Advanced Functional Materials</i> , <b>2021</b> , 31, 2005582	15.6	34
73	Optoelectronic Neuromorphic Computing: All-Optically Controlled Memristor for Optoelectronic Neuromorphic Computing (Adv. Funct. Mater. 4/2021). <i>Advanced Functional Materials</i> , <b>2021</b> , 31, 2170027	15.6	1
72	Low-Temperature Synthesis of MicroMesoporous TiO <sub>2</sub> /SiO <sub>2</sub> Composite Film Containing Fe <sup>3+</sup> Co-Doped Anatase Nanocrystals for Photocatalytic NO Removal. <i>Catalysis Letters</i> , <b>2021</b> , 151, 2396	2.8	0
71	Emerging Artificial Neuron Devices for Probabilistic Computing. <i>Frontiers in Neuroscience</i> , <b>2021</b> , 15, 717947	4.7	2
70	Ultralow operation voltages of a transparent memristor based on bilayer ITO. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 221602	3.4	10
69	Specific phase modulation and infrared photon confinement in solar selective absorbers. <i>Applied Materials Today</i> , <b>2020</b> , 18, 100533	6.6	6
68	Broadband Optoelectronic Synaptic Thin-Film Transistors Based on Oxide Semiconductors. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2020</b> , 14, 1900630	2.5	10
67	Electrochromism of Nanocrystal-in-Glass Tungsten Oxide Thin Films under Various Conduction Cations. <i>Inorganic Chemistry</i> , <b>2019</b> , 58, 2089-2098	5.1	29
66	Optoelectronic neuromorphic thin-film transistors capable of selective attention and with ultra-low power dissipation. <i>Nano Energy</i> , <b>2019</b> , 62, 772-780	17.1	48
65	Memristors based on amorphous ZnSnO films. <i>Materials Letters</i> , <b>2019</b> , 249, 169-172	3.3	10
64	Photonic Synapses for Ultrahigh-Speed Neuromorphic Computing. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2019</b> , 13, 1900082	2.5	28
63	Aqueous solution-processed, self-flattening AlO <sub>x</sub> :Y dielectrics for fully-transparent thin-film transistors. <i>Ceramics International</i> , <b>2019</b> , 45, 15883-15891	5.1	4
62	Memristive Synapses for Brain-Inspired Computing. <i>Advanced Materials Technologies</i> , <b>2019</b> , 4, 1800544	6.8	37
61	Broadband hyperbolic metamaterial covering the whole visible-light region. <i>Optics Letters</i> , <b>2019</b> , 44, 2970-2973	3	7
60	Flexible Electrochromic V <sub>2</sub> O <sub>5</sub> Thin Films with Ultrahigh Coloration Efficiency on Graphene Electrodes. <i>Journal of the Electrochemical Society</i> , <b>2018</b> , 165, D183-D189	3.9	18
59	Structural and Electrochromic Properties of Undoped and Mo-Doped V <sub>2</sub> O <sub>5</sub> Thin Films by a Two-Electrode Electrodeposition. <i>Journal of Nanoscience and Nanotechnology</i> , <b>2018</b> , 18, 7502-7507	1.3	3

58	Band Offset Engineering in ZnSnN <sub>2</sub> -Based Heterojunction for Low-Cost Solar Cells. <i>ACS Photonics</i> , <b>2018</b> , 5, 2094-2099	6.3	25
57	Thin Film Solar Cell Based on ZnSnN <sub>2</sub> /SnO Heterojunction. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2018</b> , 12, 1700332	2.5	22
56	Template-Free Growth of Well-Ordered Silver Nano Forest/Ceramic Metamaterial Films with Tunable Optical Responses. <i>Advanced Materials</i> , <b>2017</b> , 29, 1605324	24	32
55	Ultrasensitive Memristive Synapses Based on Lightly Oxidized Sulfide Films. <i>Advanced Materials</i> , <b>2017</b> , 29, 1606927	24	127
54	Coexistence of two types of metal filaments in oxide memristors. <i>AIP Advances</i> , <b>2017</b> , 7, 025102	1.5	4
53	High-temperature tolerance in WTi-Al <sub>2</sub> O <sub>3</sub> cermet-based solar selective absorbing coatings with low thermal emissivity. <i>Nano Energy</i> , <b>2017</b> , 37, 232-241	17.1	84
52	Combined control of the cation and anion to make ZnSnON thin films for visible-light phototransistors with high responsivity. <i>Journal of Materials Chemistry C</i> , <b>2017</b> , 5, 6480-6487	7.1	7
51	The same batch enabled threshold voltage tuning for vertically- or laterally-gated transparent InZnO thin-film transistors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2017</b> , 214, 1600918 <sup>6</sup>	1.6	6
50	Control of ZnO nanowire growth and optical properties in a vapor deposition process. <i>Journal of Materials Science and Technology</i> , <b>2017</b> , 33, 850-855	9.1	15
49	Proton conducting sodium-alginate-gated oxide thin-film transistors with varying device structure. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2016</b> , 213, 3103-3109	1.6	4
48	Effect of post-annealing on structural and electrochromic properties of Mo-doped V <sub>2</sub> O <sub>5</sub> thin films. <i>Journal of Sol-Gel Science and Technology</i> , <b>2016</b> , 77, 604-609	2.3	13
47	Plasmonic AgAl Bimetallic Alloy Nanoparticle/Al <sub>2</sub> O <sub>3</sub> Nanocermet Thin Films with Robust Thermal Stability for Solar Thermal Applications. <i>Advanced Materials Interfaces</i> , <b>2016</b> , 3, 1600248	4.6	20
46	The electrical properties of n-ZnO/p-SnO heterojunction diodes. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 123507	9.7	15
45	Anomalous rectification in a purely electronic memristor. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 143505	3.4	14
44	Semiconducting ZnSnN <sub>2</sub> thin films for Si/ZnSnN <sub>2</sub> p-n junctions. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 142104	3.4	44
43	Synaptic devices based on purely electronic memristors. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 013504	3.4	52
42	Single-crystalline metal filament-based resistive switching in a nitrogen-doped carbon film containing conical nanopores. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 083104	3.4	17
41	Mechanism for resistive switching in chalcogenide-based electrochemical metallization memory cells. <i>AIP Advances</i> , <b>2015</b> , 5, 057125	1.5	41

40	Determination of some basic physical parameters of SnO based on SnO/Si pn heterojunctions. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 132102	3-4	43
39	Silver nanoparticles with an armor layer embedded in the alumina matrix to form nanocermet thin films with sound thermal stability. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2014</b> , 6, 11550-7	9-5	23
38	Substrate biasing effect on the physical properties of reactive RF-magnetron-sputtered aluminum oxide dielectric films on ITO glasses. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2014</b> , 6, 2255-61	9-5	30
37	Forming-free resistive switching in a nanoporous nitrogen-doped carbon thin film with ready-made metal nanofilaments. <i>Carbon</i> , <b>2014</b> , 76, 459-463	10.4	16
36	Advances in Resistive Switching Memories Based on Graphene Oxide <b>2013</b> ,		2
35	Nonvolatile bistable resistive switching in a new polyimide bearing 9-phenyl-9H-carbazole pendant. <i>Journal of Materials Chemistry</i> , <b>2012</b> , 22, 520-526		69
34	Structural, chemical, optical, and electrical evolution of SnO(x) films deposited by reactive rf magnetron sputtering. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2012</b> , 4, 5673-7	9-5	93
33	Electrically controlled electron transfer and resistance switching in reduced graphene oxide noncovalently functionalized with thionine. <i>Journal of Materials Chemistry</i> , <b>2012</b> , 22, 16422		33
32	Ambipolar inverters using SnO thin-film transistors with balanced electron and hole mobilities. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 263502	3-4	72
31	Mechanism for resistive switching in an oxide-based electrochemical metallization memory. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 072101	3-4	107
30	Effect of top electrodes on photovoltaic properties of polycrystalline BiFeO <sub>3</sub> based thin film capacitors. <i>Nanotechnology</i> , <b>2011</b> , 22, 195201	3-4	127
29	Mechanism of nonvolatile resistive switching in graphene oxide thin films. <i>Carbon</i> , <b>2011</b> , 49, 3796-3802	10.4	124
28	Roles of silver oxide in the bipolar resistance switching devices with silver electrode. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 072107	3-4	39
27	Improvement of resistive switching in Cu/ZnO/Pt sandwiches by weakening the randomness of the formation/rupture of Cu filaments. <i>Nanotechnology</i> , <b>2011</b> , 22, 275204	3-4	91
26	Microstructure dependence of leakage and resistive switching behaviours in Ce-doped BiFeO <sub>3</sub> thin films. <i>Journal Physics D: Applied Physics</i> , <b>2011</b> , 44, 415104	3	40
25	Nonvolatile resistive switching memory based on amorphous carbon. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 163505	3-4	123
24	Improvement of reproducible resistance switching in polycrystalline tungsten oxide films by in situ oxygen annealing. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 072103	3-4	68
23	Resistance switching in polycrystalline BiFeO <sub>3</sub> thin films. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 042101	3-4	129

22	Nonvolatile resistive switching in metal/La-doped BiFeO <sub>3</sub> /Pt sandwiches. <i>Nanotechnology</i> , <b>2010</b> , 21, 425202	3.4	94
21	Nonvolatile resistive switching in graphene oxide thin films. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 232101	3.4	192
20	Ternary compound B <sub>4</sub> CN <sub>4</sub> prepared by direct nitridation of B <sub>4</sub> C. <i>Journal of Alloys and Compounds</i> , <b>2008</b> , 466, 299-303	5.7	5
19	Preparation and photoluminescent investigation of h-BN-like layered material B <sub>4</sub> CN <sub>4</sub> . <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 3869-3872	1.6	6
18	ZnO light-emitting diodes fabricated on Si substrates with homobuffer layers. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 113503	3.4	67
17	Al concentration dependence of electrical and photoluminescent properties of co-doped ZnO films. <i>Chemical Physics Letters</i> , <b>2007</b> , 437, 203-206	2.5	16
16	Strain and its effect on optical properties of Al-N codoped ZnO films. <i>Journal of Applied Physics</i> , <b>2006</b> , 99, 023503	2.5	86
15	Electrical characterization of ZnO-based homojunctions. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 053501	3.4	51
14	Defect-related vibrational and photoluminescence spectroscopy of a codoped ZnO : Al : N film. <i>Journal Physics D: Applied Physics</i> , <b>2006</b> , 39, 2339-2342	3	13
13	Carrier localization in codoped ZnO:N:Al films. <i>Solid State Communications</i> , <b>2006</b> , 138, 542-545	1.6	14
12	Reproducibility and stability of N/Al codoped p-type ZnO thin films. <i>Journal of Materials Science</i> , <b>2006</b> , 41, 467-470	4.3	14
11	ZnO p-n homojunctions and ohmic contacts to Al/N-co-doped p-type ZnO. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 092103	3.4	86
10	Improved N/Al codoped p-type ZnO thin films by introduction of a homo-buffer layer. <i>Journal of Crystal Growth</i> , <b>2005</b> , 274, 425-429	1.6	20
9	Rapid synthesis and photoluminescence of novel ZnO nanotetrapods. <i>Journal of Crystal Growth</i> , <b>2005</b> , 274, 447-452	1.6	38
8	Formation of quasi-aligned ZnCdO nanorods and nanoneedles. <i>Journal of Crystal Growth</i> , <b>2005</b> , 283, 373-377	3.7	37
7	p-type ZnO films by codoping of nitrogen and aluminum and ZnO-based p/n homojunctions. <i>Journal of Crystal Growth</i> , <b>2005</b> , 283, 413-417	1.6	24
6	Effects of growth ambient on electrical properties of Al/N co-doped p-type ZnO films. <i>Thin Solid Films</i> , <b>2005</b> , 476, 272-275	2.2	17
5	Al/N codoping and p-type conductivity in ZnO using different nitrogen sources. <i>Surface and Coatings Technology</i> , <b>2005</b> , 198, 354-356	4.4	13

4	Dependence of properties of NAl codoped p-type ZnO thin films on growth temperature. <i>Applied Surface Science</i> , <b>2005</b> , 245, 109-113	6.7	19
3	p-type conduction in NAl co-doped ZnO thin films. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 3134-3135	3.4	208
2	Nanocomposite W <sub>0.5</sub> ThO <sub>2</sub> thermionic cathode. <i>Materials Letters</i> , <b>2003</b> , 57, 2776-2779	3.3	23
1	Retina-Inspired Two-Terminal Optoelectronic Neuromorphic Devices with Light-Tunable Short-Term Plasticity for Self-Adjusting Sensing. <i>Advanced Intelligent Systems</i> , 2200019	6	7